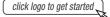


# Hyperfast Rectifier, 3 A FRED Pt®



#### **DESIGN SUPPORT TOOLS**





| PRIMARY CHARACTERISTICS          |                    |  |  |  |
|----------------------------------|--------------------|--|--|--|
| I <sub>F(AV)</sub>               | 3 A                |  |  |  |
| $V_{R}$                          | 200 V              |  |  |  |
| V <sub>F</sub> at I <sub>F</sub> | 0.74 V             |  |  |  |
| t <sub>rr</sub>                  | 30 ns              |  |  |  |
| T <sub>J</sub> max.              | 175 °C             |  |  |  |
| Package                          | SlimSMA (DO-221AC) |  |  |  |
| Circuit configuration            | Single             |  |  |  |

#### **FEATURES**

 Hyperfast recovery time, reduced Q<sub>rr</sub>, and soft recovery



COMPLIANT HALOGEN

**FREE** 

- 175 °C maximum operating junction temperature
- Specific for output and snubber operation
- Low forward voltage drop
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

#### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, piezo-injection, as high frequency rectifiers and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

| ABSOLUTE MAXIMUM RATINGS                    |                                   |  |             |       |  |
|---|-----------------------------------|--|-------------|-------|--|
| PARAMETER                                   | SYMBOL                            | TEST CONDITIONS                        | VALUES      | UNITS |  |
| Peak repetitive reverse voltage             | $V_{RRM}$                         |  | 200         | V     |  |
| Average rectified forward current           | I <sub>F(AV)</sub>                | T <sub>C</sub> = 145 °C <sup>(1)</sup> | 3           | ۸     |  |
| Non-repetitive peak surge current           | I <sub>FSM</sub>                  | T <sub>J</sub> = 25 °C                 | 85          | - A   |  |
| Operating junction and storage temperatures | T <sub>J</sub> , T <sub>Stg</sub> |  | -65 to +175 | °C    |  |

#### Note

<sup>(1)</sup> Device on PCB with 8 mm x 16 mm soldering lands

| <b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified) |                                     |  |      |      |      |       |
|--|-------------------------------------|--|------|------|------|-------|
| PARAMETER  | SYMBOL                              | TEST CONDITIONS  | MIN. | TYP. | MAX. | UNITS |
| Breakdown voltage,<br>blocking voltage   | V <sub>BR</sub> ,<br>V <sub>R</sub> | I <sub>R</sub> = 100 μA                                | 200  | -    | -    | .,    |
| Forward voltage  | V <sub>F</sub>                      | I <sub>F</sub> = 3 A                                   | -    | 0.86 | 0.93 | V     |
| i orward voitage   | ٧F                                  | I <sub>F</sub> = 3 A, T <sub>J</sub> = 125 °C          | -    | 0.74 | 0.78 |       |
| Reverse leakage current  |                                     | $V_R = V_R$ rated                                      | -    | -    | 2    |       |
|  | I <sub>R</sub>                      | $T_J = 125 ^{\circ}\text{C},  V_R = V_R  \text{rated}$ | -    | 1    | 8    | μA    |
| Junction capacitance   | C <sub>T</sub>                      | V <sub>R</sub> = 200 V                                 | -    | 13   | -    | pF    |



| <b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified) |                                       |  |   |      |      |      |       |
|---|---------------------------------------|--|---|------|------|------|-------|
| PARAMETER   | SYMBOL                                | TEST CONDITIONS  |   | MIN. | TYP. | MAX. | UNITS |
|   |                                       | $I_F = 1.0 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$    |   | -    | 26   | -    |       |
| Reverse recovery time   |                                       | I <sub>F</sub> = 0.5 A, I <sub>R</sub> = 1 A, I <sub>rr</sub> = 0.25 A           |   | -    | ı    | 30   |       |
| heverse recovery time   | Reverse recovery time t <sub>rr</sub> | T <sub>J</sub> = 25 °C   |   | -    | 18   | -    | ns    |
|   |                                       | T <sub>J</sub> = 125 °C  |   | =    | 26   | -    |       |
| Peak recovery current I <sub>RRM</sub>  | T <sub>J</sub> = 25 °C                | I <sub>F</sub> = 3 A<br>dI <sub>F</sub> /dt = 200 A/μs<br>V <sub>B</sub> = 160 V | - | 2.5  | -    | — А  |       |
|   | T <sub>J</sub> = 125 °C               |  | - | 4    | -    |      |       |
| Reverse recovery charge Q <sub>rr</sub>   | 0                                     | T <sub>J</sub> = 25 °C   |   | =    | 23   | -    | nC    |
|   | T <sub>J</sub> = 125 °C               |  | - | 50   | -    | IIC  |       |

| THERMAL - MECHANICAL SPECIFICATIONS (T <sub>J</sub> = 25 °C unless otherwise specified) |                                   |  |      |        |                |       |
|---|-----------------------------------|--|------|--------|----------------|-------|
| PARAMETER   | SYMBOL                            | TEST CONDITIONS  | MIN. | TYP.   | MAX.           | UNITS |
| Maximum junction and storage temperature range  | T <sub>J</sub> , T <sub>Stg</sub> |  | -65  | -      | 175            | °C    |
| Thermal resistance, junction to lead  | R <sub>thJL</sub>                 | Device mounted on PCB with<br>8 mm x 16 mm soldering lands | -    | 8      | 10             | °C/W  |
| Thermal resistance, junction to ambient   | R <sub>thJA</sub>                 | Device mounted on PCB with 2 mm x 3.5 mm soldering lands   | -    | 91     | 110            | C/VV  |
| Approximate Weight  |                                   |  |      | 0.032  |                | g     |
| Approximate Weight  |                                   |  |      | 0.0011 |                | oz.   |
| Marking device  |                                   | Case style SlimSMA (DO-221AC)                              |      | 31     | <del>1</del> 2 |       |

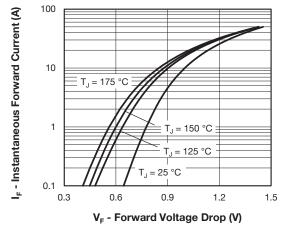


Fig. 1 - Typical Forward Voltage Drop Characteristics

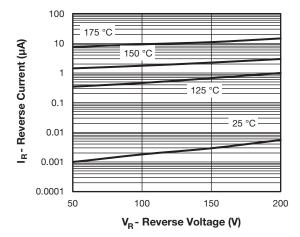


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

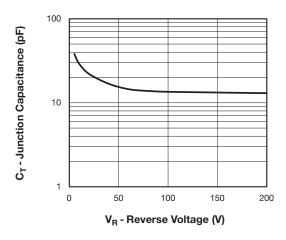


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

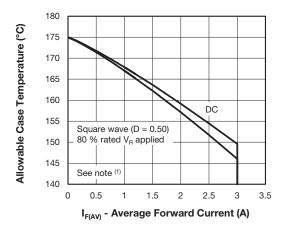


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

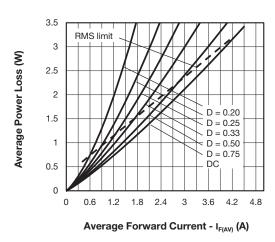


Fig. 5 - Forward Power Loss Characteristics

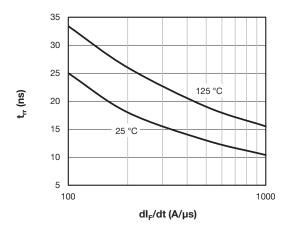


Fig. 6 - Typical Reverse Recovery vs. dI<sub>F</sub>/dt

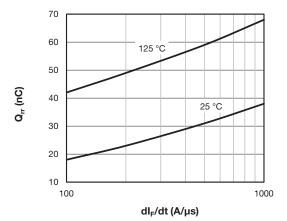


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

 $^{(1)}$  Formula used: T<sub>C</sub> = T<sub>J</sub> - (Pd + Pd<sub>REV</sub>) x R<sub>thJC</sub>; Pd = forward power loss = I<sub>F(AV)</sub> x V<sub>FM</sub> at (I<sub>F(AV)</sub>/D) (see Fig. 6); Pd<sub>REV</sub> = inverse power loss = V<sub>R1</sub> x I<sub>R</sub> (1 - D); I<sub>R</sub> at V<sub>R1</sub> = rated V<sub>R</sub>



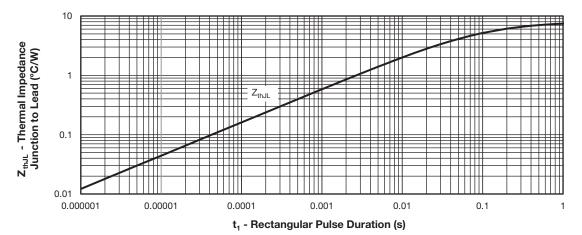


Fig. 8 - Typical Thermal Impedance Z<sub>thJL</sub> Junction-to-Lead

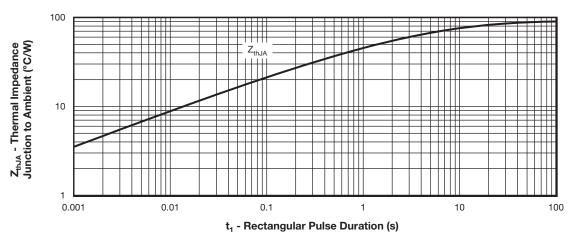
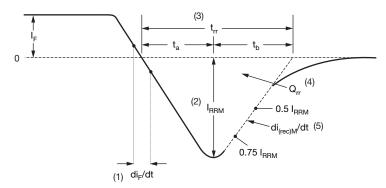


Fig. 9 - Typical Thermal Impedance  $Z_{thJA}$  Junction-to-Ambient



- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_{r}$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

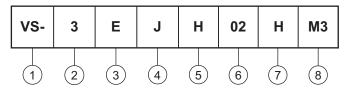
(5) di<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 10 - Reverse Recovery Waveform and Definitions



### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

**2** - Current rating (3 = 3 A)

3 - Circuit configuration:

E = single diode

4 - J = SlimSMA package

5 - Process type,

H = hyperfast recovery

6 - Voltage code (02 = 200 V)

7 - H = AEC-Q101 qualified

8 - M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

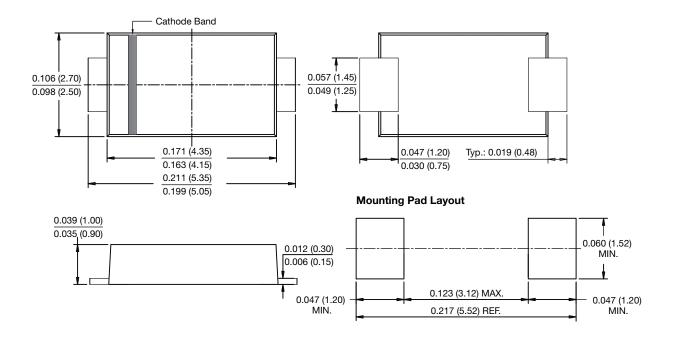
| ORDERING INFORMATION (Example) |                   |                        |                                   |  |  |
|--------------------------------|-------------------|------------------------|-----------------------------------|--|--|
| PREFERRED P/N                  | QUANTITY PER REEL | MINIMUM ORDER QUANTITY | PACKAGING DESCRIPTION             |  |  |
| VS-3EJH02HM3/6A                | 3500              | 3500                   | 7"diameter plastic tape and reel  |  |  |
| VS-3EJH02HM3/6B                | 14 000            | 14 000                 | 13"diameter plastic tape and reel |  |  |

| LINKS TO RELATED DOCUMENTS |                          |  |  |  |
|----------------------------|--------------------------|--|--|--|
| Dimensions                 | www.vishay.com/doc?95571 |  |  |  |
| Part marking information   | www.vishay.com/doc?95562 |  |  |  |
| Packaging information      | www.vishay.com/doc?88869 |  |  |  |
| SPICE model                | www.vishay.com/doc?96050 |  |  |  |



# DO-221AC (SlimSMA)

### **DIMENSIONS** in inches (millimeters)





## **Legal Disclaimer Notice**

Vishay

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